SURFACE MOUNT GENERAL PURPOSE SILICON RECTIFIERS

Forward Current-2A

Reverse Voltage-50V to 1000V

FEATURES

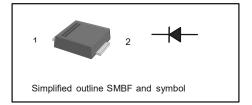
- ♦ For surface mount applications
- ♦ Glass passivated chip junction
- **♦** Low profile package
- Easy to pick and place
- ◆ Lead free in comply with EU RoHS2011/65/EU directives

MECHANICAL DATA

- ◆ Case: SMBF molded plastic body
- ◆ Terminals: Solderable per MIL-STD-750 , Method 2026
- ♦ Weight: Approximated 0.057 grams

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derating by 20 %.

PARAMETER	SYMBOL	S2ABF -AT	S2BBF -AT	S2DBF -AT	S2GBF -AT	S2JBF -AT	S2KBF -AT	S2MBF -AT	UNIT
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	٧
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current at Tc=125°C	I _{F(AV)}	2					Α		
Peak Forward Surge Current (Note1)	I _{FSM}	70					Α		
Maximum Forward Voltage at 2.0 A	VF	1.1					V		
Maximum DC Reverse Current at Rated DC Blocking Voltage at T _A =25°C T _A =125°C	I _R	5 100					uA		
Typical Junction Capacitance(Note2)	Сл	25					pF		
Typical Thermal Resistance(Note3)	RθJA RθJC	60 18					°C/W		
Operating and Storage Temperature Range	T _J ,T _{STG}	-55 to +150					°C		

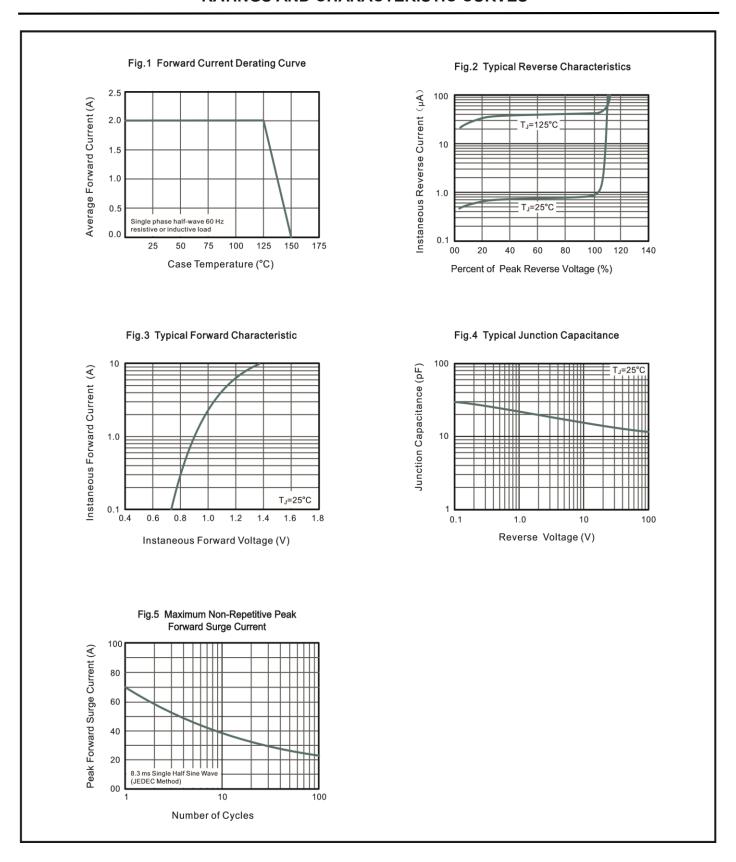
Notes: 1. Measured at 8.3 ms single half sine wave superimposed on rated load (JEDEC Method).

- 2. Measured at 1MHz and applied reverse voltage of 4V D.C.
- 3. P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

Dated: 04/2016

Rev:1.0

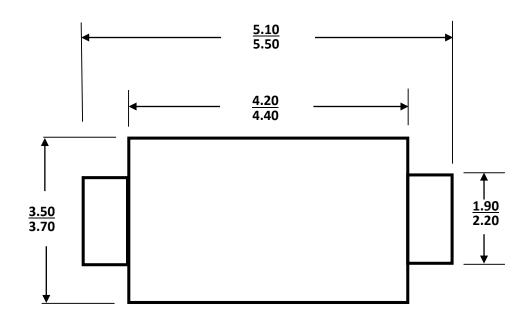
RATINGS AND CHARACTERISTIC CURVES

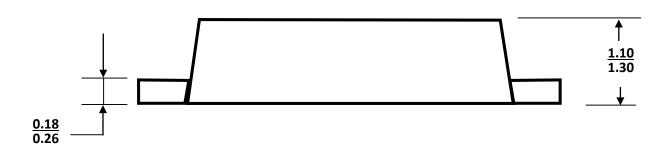


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PACKAGE OUTLINE

SMBF





Dimensions in milimeters

ORDERING INFORMATION

Device	Package	Shipping
S2ABF-AT thru S2MBF-AT	SMBF	5,000/Tape & Reel (13 inches)

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